

**ADVANCED
POWER
TECHNOLOGY®**

APT10050JN 1000V 20.5A 0.50Ω



"UL Recognized" File No. E145592 (S)

POWER MOS IV®

SINGLE DIE ISOTOP® PACKAGE

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter		APT 10050JN	UNIT
V_{DSS}	Drain-Source Voltage		1000	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$		20.5	Amps
I_{DM}, I_{LM}	Pulsed Drain Current ^① and Inductive Current Clamped		82	
V_{GS}	Gate-Source Voltage	± 30		Volts
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	520		Watts
	Linear Derating Factor	4.16		W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150		$^\circ\text{C}$
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250 \mu\text{A}$)	APT10050JN 1000			Volts
$I_{D(ON)}$	On State Drain Current ^② ($V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max, $V_{GS} = 10V$)	APT10050JN 20.5			Amps
$R_{DS(ON)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10V, 0.5 I_D$ [Cont.])	APT10050JN 0.50			Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 2.5\text{mA}$)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.24	$^\circ\text{C/W}$
$R_{\theta CS}$	Case to Sink (Use High Efficiency Thermal Joint Compound and Planer Heat Sink Surface.)		0.06		



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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DYNAMIC CHARACTERISTICS

APT10050JN

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1 \text{ MHz}$		5425	6500	pF
C_{oss}	Output Capacitance			710	995	
C_{rss}	Reverse Transfer Capacitance			230	350	
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$		235	370	nC
Q_{gs}	Gate-Source Charge			24	36	
Q_{gd}	Gate-Drain ("Miller") Charge			107	160	
$t_d(\text{on})$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^\circ\text{C}$ $R_G = 0.6\Omega$		15	30	ns
t_r	Rise Time			15	30	
$t_d(\text{off})$	Turn-off Delay Time			47	75	
t_f	Fall Time			15	30	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT10050JN			20.5	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)	APT10050JN			82	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V$, $I_S = -I_D [\text{Cont.}]$)				1.8	Volts
t_{rr}	Reverse Recovery Time ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)			1280	2000	ns
Q_{rr}	Reverse Recovery Charge ($I_S = -I_D [\text{Cont.}]$, $dI_S/dt = 100A/\mu s$)			16	32	μC

PACKAGE CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
L_D	Internal Drain Inductance (Measured From Drain Terminal to Center of Die.)		3		nH
L_S	Internal Source Inductance (Measured From Source Terminals to Source Bond Pads)		5		
$V_{isolation}$	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
$C_{isolation}$	Drain-to-Mounting Base Capacitance ($f = 1\text{MHz}$)		35		pF
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations.			13	in-lbs

① Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig.1)

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

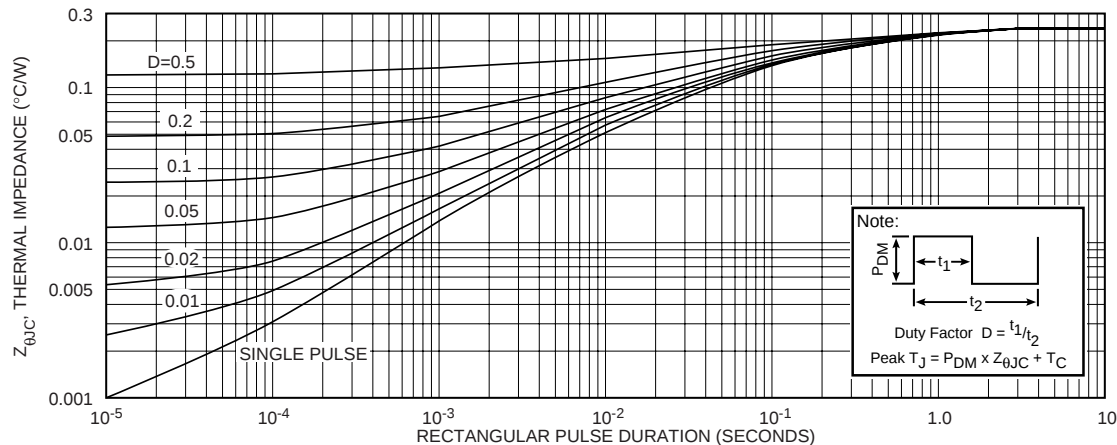


FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

APT10050JN

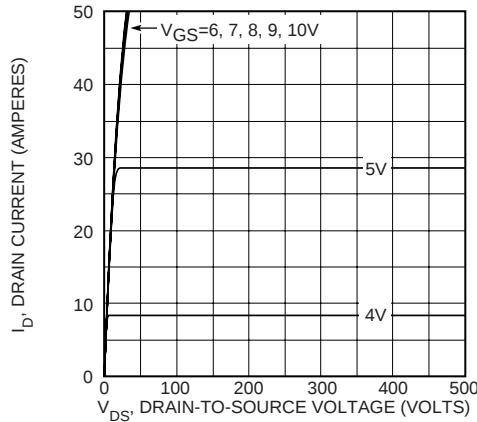


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

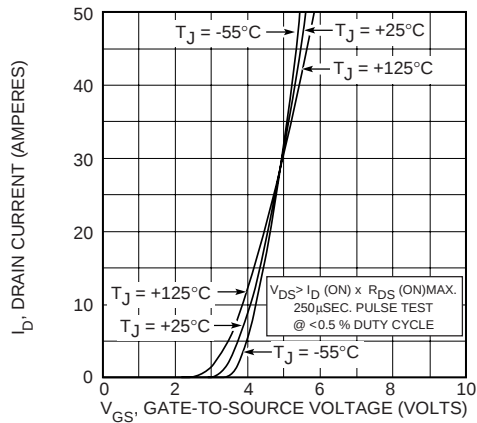


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

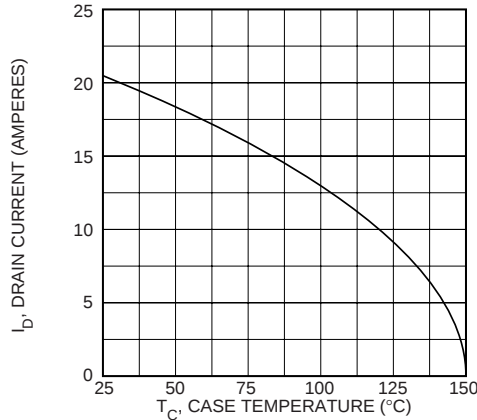


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

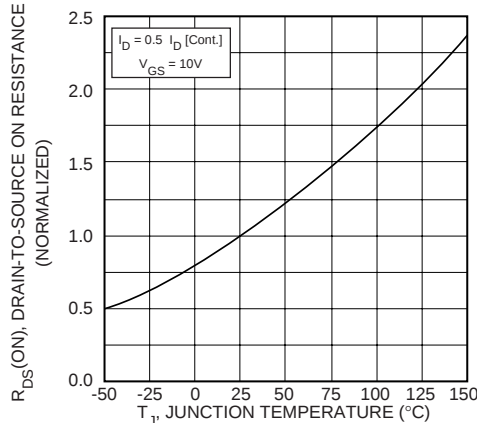


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

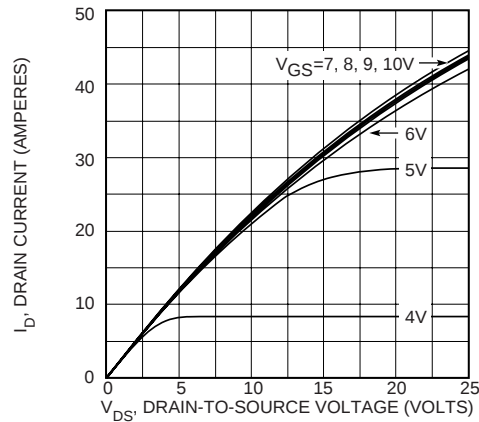


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

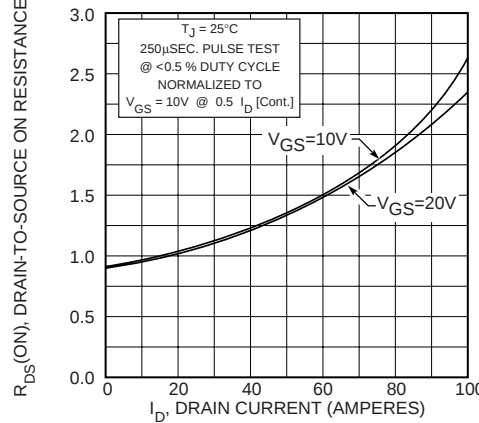


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

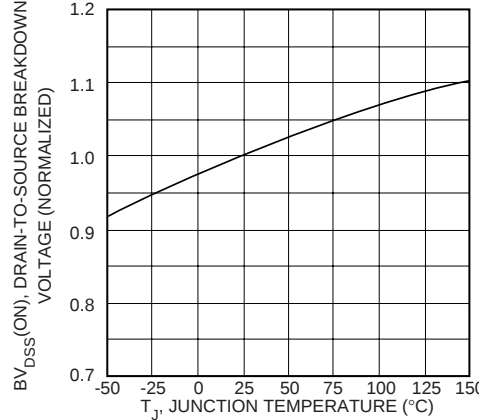


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

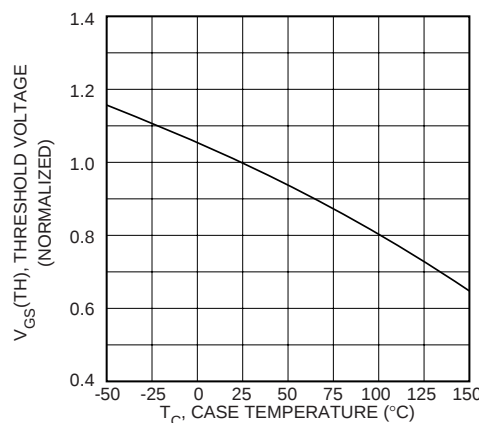


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

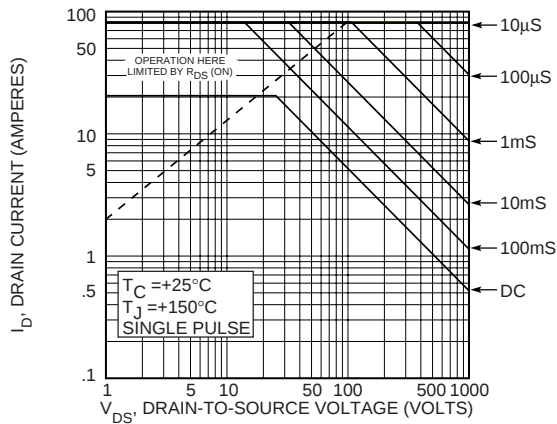


FIGURE 10, MAXIMUM SAFE OPERATING AREA

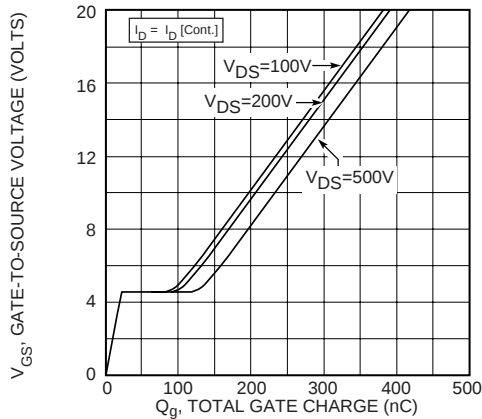


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

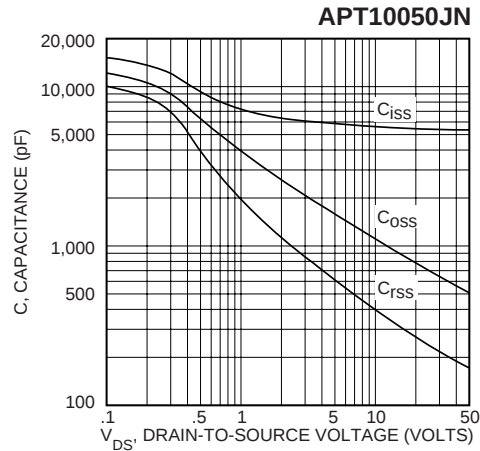


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

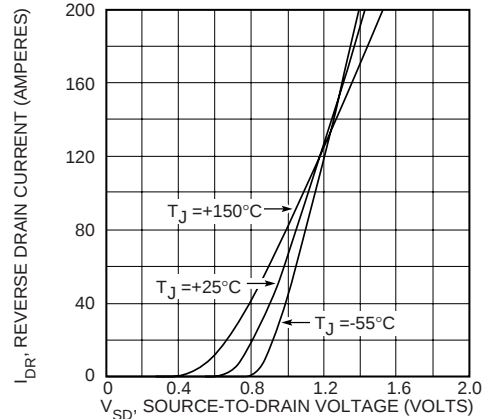
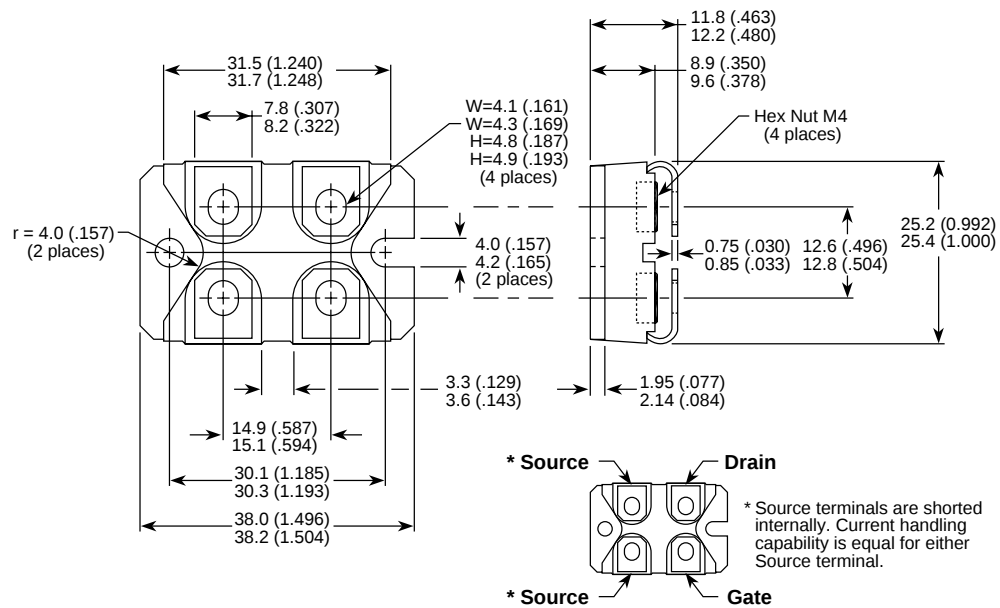


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

APT Reserves the right to change, without notice, the specifications and information contained herein.

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

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